L Number	Hits	Search Text	DB	Time stamp
1	41	(US-6743695-\$ or US-6682985-\$ or	USPAT;	2004/10/05 09:20
		US-6180490-\$ or US-6100163-\$ or	US-PGPUB	2004, 10, 03 03:20
		US-6074954-\$ or US-6495903-\$ or	10102	
		US-6180995-\$ or US-6287931-\$ or		
		US-6221727-\$ or US-6770537-\$ or		
		US-6756653-\$ or US-6413827-\$ or		
		US-6486061-\$ or US-6383913-\$ or		
		US-6348407-\$ or US-6716742-\$ or		
		US-6399432-\$ or US-6693011-\$ or		i
		US-6689664-\$ or US-6521923-\$ or		
]	US-6686627-\$ or US-6153905-\$ or		
		US-5869875-\$ or US-5918137-\$ or		
		US-6215152-\$ or US-6091110-\$).did. or		
		(US-5949104-\$ or US-5841166-\$ or		
		US-5252848-\$ or US-6271552-\$ or		
		US-6190978-\$ or US-6222233-\$ or		
		US-6048772-\$ or US-6034415-\$ or		
	1	US-5900663-\$ or US-6716770-\$).did. or		
		(US-20040069410-\$ or US-20040166240-\$ or		
		US-20040156987-\$ or US-20040023453-\$ or		
		US-20030129827-\$).did.		
2	8	((((silicon near1 precursor) and (cvd	USPAT;	2004/10/05 09:37
	Ī	(chemical near1 vapor near1 deposition)))	US-PGPUB;	2003, 20, 03 03.3.
		and (low near1 dielectric)) and (cmp	EPO; JPO	
		(chemical near1 mechanical near1		
		polishing))) and (omcts		
		octamethylcyclotetrasiloxane tmcts		
		tetramethylcyclotetrasiloxane)		
3	106		USPAT;	2004/10/05 09:37
!		vapor nearl deposition))) and (low nearl	US-PGPUB;	, ,
		dielectric)) and (cmp (chemical near1	EPO; JPO	
		mechanical near1 polishing))) and (omcts		1
		octamethylcyclotetrasiloxane tmcts		
		tetramethylcyclotetrasiloxane)		
4	17	((((silicon near3 precursor) and (cvd	USPAT;	2004/10/05 09:37
		<pre>(chemical near1 vapor near1 deposition)))</pre>	US-PGPUB;	
		and (low nearl dielectric)) and (cmp	EPO; JPO	
		(chemical near1 mechanical near1		1
		polishing))) and (omcts		
		octamethylcyclotetrasiloxane tmcts		
		tetramethylcyclotetrasiloxane)		
5	9	(((((silicon near3 precursor) and (cvd	USPAT;	2004/10/05 09:37
		(chemical near1 vapor near1 deposition)))	US-PGPUB;	
		and (low near1 dielectric)) and (cmp	EPO; JPO	
		(chemical near1 mechanical near1		i
		polishing))) and (omcts	1	
		octamethylcyclotetrasiloxane tmcts		l
		tetramethylcyclotetrasiloxane)) not	1	
•		(((((silicon near1 precursor) and (cvd		
		(chemical near1 vapor near1 deposition)))		
		and (low near1 dielectric)) and (cmp		
		(chemical near1 mechanical near1		
		<pre>polishing))) and (omcts octamethylcyclotetrasiloxane tmcts</pre>	1	ĺ
				ł
6	14	tetramethylcyclotetrasiloxane)) ("3510369" "4872947" "4895734"	HEDAM	2004/10/05 00 40
ا ۱	14	("3510369" "4872947" "4895734" "4951601" "5011706" "5086014"	USPAT	2004/10/05 09:40
		"5242530" "5298597" "5360491"		
		"5465680"	1	
		"6054379" "6147009" "2002/0111042"	1	
		"2003/0003765" "2003/0003768"		
	†	"2003/0089988" "2003/0111730"		-
		"2003/0129827").PN.		
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